

XG0028

N-Channel Enhancement Mode SGT MOSFET

100V(VDS) / ± 20 V(VGS) / 80A(ID)

Rev0.2

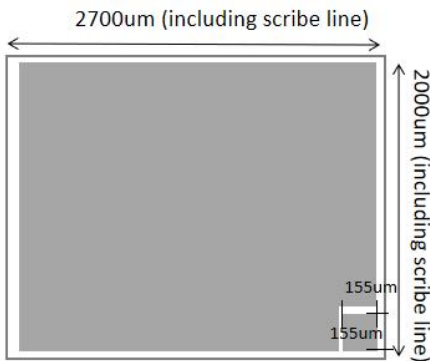
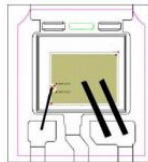


Wafer Specification

1. Order Information

Part No.	Description	Gross die / per 8" wafer
XG0028	100V(V_{DS}) / $\pm 20V(V_{GS})$/ 80 A(I_D) N-Channel Enhancement Mode SGT MOSFET	5,200

2. Physical Characteristics

	Die Size: 2700 μ m $\times$ 2000 μ m (including scribe line)
	Gate: 155 μ m $\times$ 155 μ m
	For TO-252-3L package Suggest Bonding wire: Gate: 1*5mil Cu Source: 2*15mil AL 

3. Mechanical Data

Nominal Back Metal Composition, Thickness	Ti-Ni-Ag (13kA°)
Nominal Front Metal Composition, Thickness	AlCu (4 μ m)
Wafer Diameter	200mm, with 010 notch
Wafer Thickness	200 $\pm$ 10 μ m
Scribe Line Width	60 μ m

4. Key Electrical Characteristics of Die (at T_J = 25 °C, unless otherwise specified)S

Parameter	Description	Min.	Typ.	Max.	Unit	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100			V	$V_{GS}=0V$, $I_D=250\mu A$
$I_{D(Device Ref)}$	Continuous Drain Current			80	A	$T_J=25^{\circ}C$
$R_{DS(on)(FT)}$	Static Drain-to-Source On-Resistance		5.9	7.4	m Ω	$V_{GS}=10V$, $I_D=20A$
$V_{GS(th)}$	Gate Threshold Voltage	1.2	1.7	2.2	V	$V_{DS}=V_{GS}$, $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS}=80V$, $V_{GS}=0V$
I_{GSS}	Gate-to-Source Leakage Current			± 100	nA	$V_{GS}=\pm 20V$, $V_{DS}=0V$
T_J , T_{STG}	Operating and Storage Temperature	-55 $^{\circ}C$ to 150 $^{\circ}C$ Max				